irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

6. (Thrice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition;

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

11. (Thrice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS;

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

30. (Thrice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a crystalline semiconductor film over a substrate;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition;

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

34. (Thrice Amended) A method for manufacturing a semiconductor device